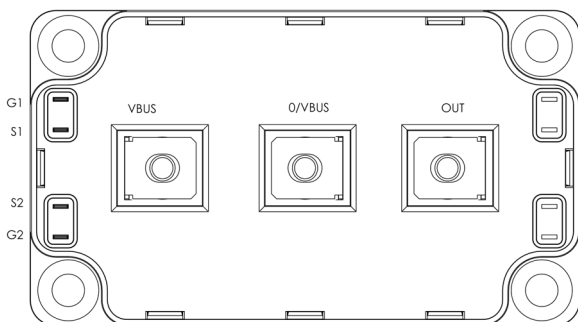
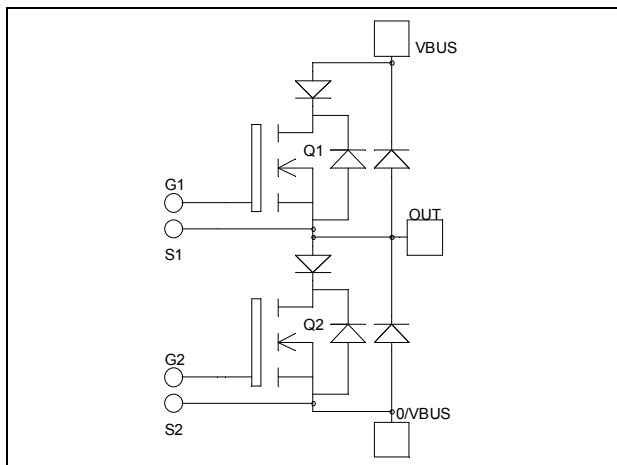


*Phase leg
Series & parallel diodes
MOSFET Power Module*

$$V_{DSS} = 1000V$$

$$R_{DSon} = 130m\Omega \text{ typ @ } T_j = 25^\circ C$$

$$I_D = 65A \text{ @ } T_c = 25^\circ C$$


Application

- Motor control
- Switched Mode Power Supplies
- Uninterruptible Power Supplies

Features

- Power MOS 7[®] MOSFETs
 - Low R_{DSon}
 - Low input and Miller capacitance
 - Low gate charge
 - Fast intrinsic reverse diode
 - Avalanche energy rated
 - Very rugged
- Kelvin source for easy drive
- Very low stray inductance
 - Symmetrical design
 - M5 power connectors
- High level of integration

Benefits

- Outstanding performance at high frequency operation
- Direct mounting to heatsink (isolated package)
- Low junction to case thermal resistance
- Low profile
- RoHS Compliant

All ratings @ $T_j = 25^\circ C$ unless otherwise specified

Absolute maximum ratings

Symbol	Parameter	Max ratings	Unit
V_{DSS}	Drain - Source Breakdown Voltage	1000	V
I_D	Continuous Drain Current	$T_c = 25^\circ C$	A
		$T_c = 80^\circ C$	
I_{DM}	Pulsed Drain current	240	
V_{GS}	Gate - Source Voltage	± 30	V
R_{DSon}	Drain - Source ON Resistance	156	m Ω
P_D	Maximum Power Dissipation	$T_c = 25^\circ C$	W
I_{AR}	Avalanche current (repetitive and non repetitive)	24	A
E_{AR}	Repetitive Avalanche Energy	30	mJ
E_{AS}	Single Pulse Avalanche Energy	1300	

CAUTION: These Devices are sensitive to Electrostatic Discharge. Proper Handling Procedures Should Be Followed. See application note APT0502 on www.microsemi.com

Electrical Characteristics

Symbol	Characteristic	Test Conditions	Min	Typ	Max	Unit
I _{DSS}	Zero Gate Voltage Drain Current	V _{GS} = 0V, V _{DS} = 1000V			600	μA
		V _{GS} = 0V, V _{DS} = 800V			2	mA
R _{DS(on)}	Drain – Source on Resistance	V _{GS} = 10V, I _D = 32.5A		130	156	mΩ
V _{GS(th)}	Gate Threshold Voltage	V _{GS} = V _{DS} , I _D = 6mA	3		5	V
I _{GSS}	Gate – Source Leakage Current	V _{GS} = ±30 V, V _{DS} = 0V			±450	nA

Dynamic Characteristics

Symbol	Characteristic	Test Conditions	Min	Typ	Max	Unit
C _{iss}	Input Capacitance	V _{GS} = 0V		15.2		nF
C _{oss}	Output Capacitance	V _{DS} = 25V		2.6		
C _{rss}	Reverse Transfer Capacitance	f = 1MHz		0.42		
Q _g	Total gate Charge	V _{GS} = 10V		562		nC
Q _{gs}	Gate – Source Charge	V _{Bus} = 500V		75		
Q _{gd}	Gate – Drain Charge	I _D = 65A		363		
T _{d(on)}	Turn-on Delay Time	Inductive switching @ 125°C V _{GS} = 15V V _{Bus} = 667V I _D = 65A R _G = 0.5Ω		9		ns
T _r	Rise Time			9		
T _{d(off)}	Turn-off Delay Time			50		
T _f	Fall Time			24		
E _{on}	Turn-on Switching Energy	Inductive switching @ 25°C V _{GS} = 15V, V _{Bus} = 667V I _D = 65A, R _G = 0.5Ω		2.13		mJ
E _{off}	Turn-off Switching Energy			0.46		
E _{on}	Turn-on Switching Energy	Inductive switching @ 125°C V _{GS} = 15V, V _{Bus} = 667V I _D = 65A, R _G = 0.5Ω		4.4		mJ
E _{off}	Turn-off Switching Energy			0.57		
R _{thJC}	Junction to Case Thermal Resistance				0.1	°C/W

Series diode ratings and characteristics

Symbol	Characteristic	Test Conditions	Min	Typ	Max	Unit
V _{RRM}	Maximum Repetitive Reverse Voltage		1000			V
I _{RM}	Maximum Reverse Leakage Current	V _R = 1000V			350	μA
I _F	DC Forward Current	T _c = 100°C		120		A
V _F	Diode Forward Voltage	I _F = 120A		1.9	2.5	V
		I _F = 240A		2.2		
		I _F = 120A, T _j = 125°C		1.7		
t _{rr}	Reverse Recovery Time	I _F = 120A V _R = 667V di/dt = 400A/μs	T _j = 25°C	280		ns
			T _j = 125°C	350		
Q _{rr}	Reverse Recovery Charge	I _F = 120A V _R = 667V di/dt = 400A/μs	T _j = 25°C	1520		nC
			T _j = 125°C	7200		
R _{thJC}	Junction to Case Thermal Resistance				0.46	°C/W

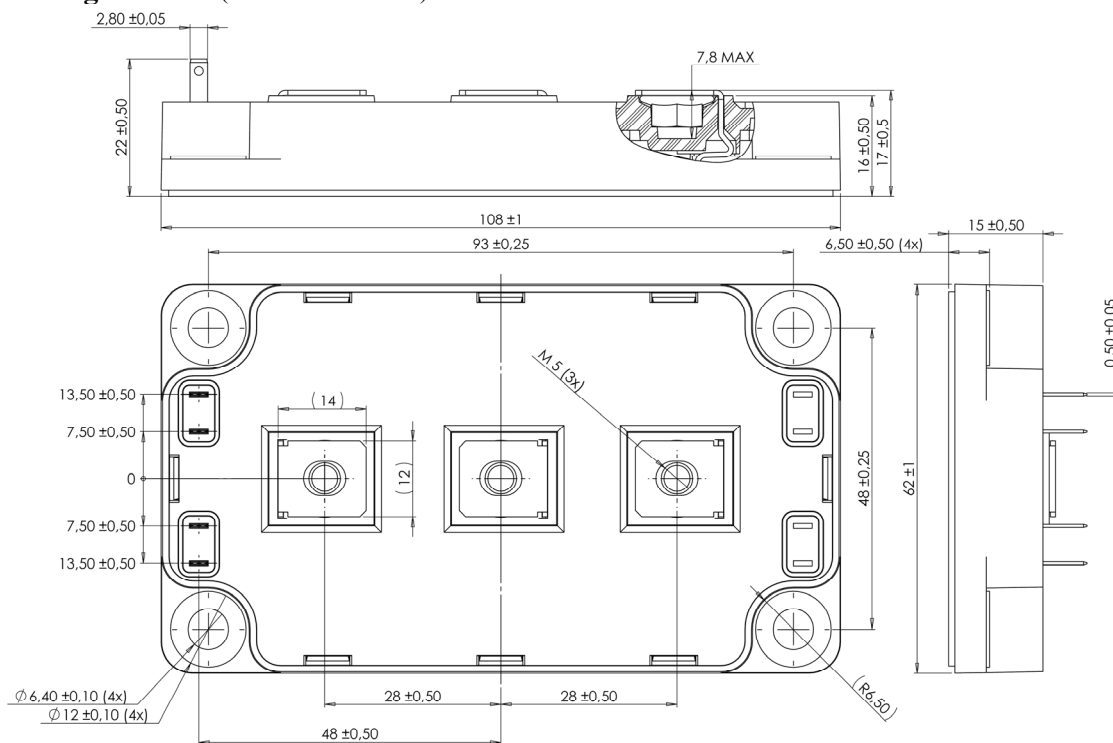
Parallel diode ratings and characteristics

Symbol	Characteristic	Test Conditions		Min	Typ	Max	Unit
V _{RRM}	Maximum Repetitive Reverse Voltage			1000			V
I _{RM}	Maximum Reverse Leakage Current	V _R =1000V				350	μA
I _F	DC Forward Current		T _c = 100°C		120		A
V _F	Diode Forward Voltage	I _F = 120A			1.9	2.5	V
		I _F = 240A			2.2		
		I _F = 120A	T _j = 125°C		1.7		
t _{rr}	Reverse Recovery Time	I _F = 120A V _R = 667V di/dt = 400A/μs	T _j = 25°C		280		ns
			T _j = 125°C		350		
Q _{rr}	Reverse Recovery Charge		T _j = 25°C		1520		nC
			T _j = 125°C		7200		
R _{thJC}	Junction to Case Thermal Resistance					0.46	°C/W

Thermal and package characteristics

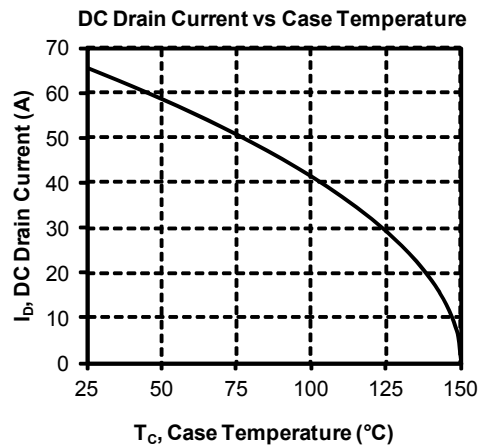
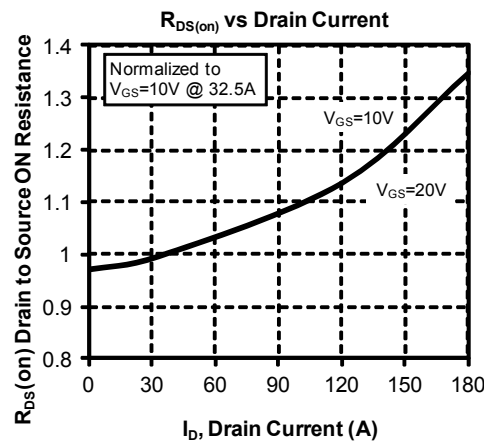
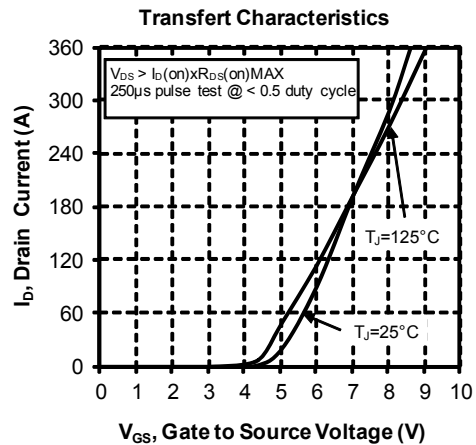
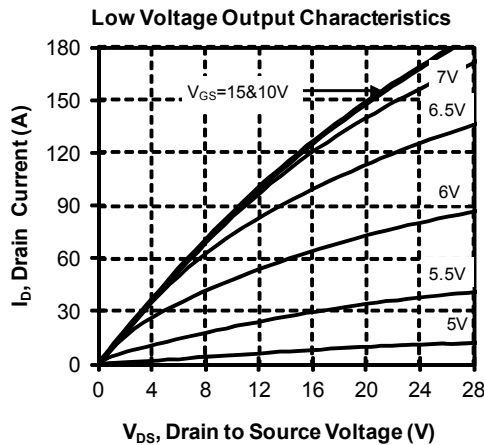
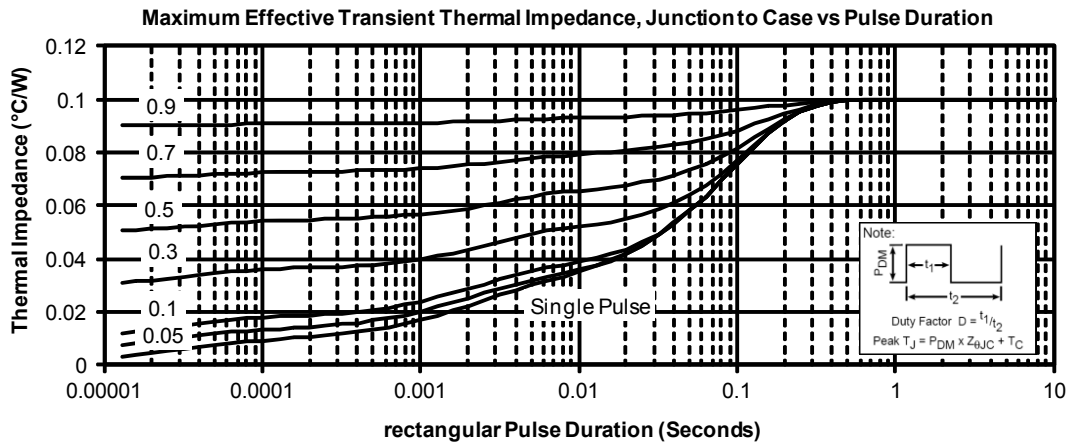
Symbol	Characteristic	Min	Typ	Max	Unit
V _{ISOL}	RMS Isolation Voltage, any terminal to case t=1 min, 50/60Hz	4000			V
T _J	Operating junction temperature range	-40		150	°C
T _{STG}	Storage Temperature Range	-40		125	
T _C	Operating Case Temperature	-40		100	
Torque	Mounting torque	To heatsink	M6	3	N.m
		For terminals	M5	2	
Wt	Package Weight			300	g

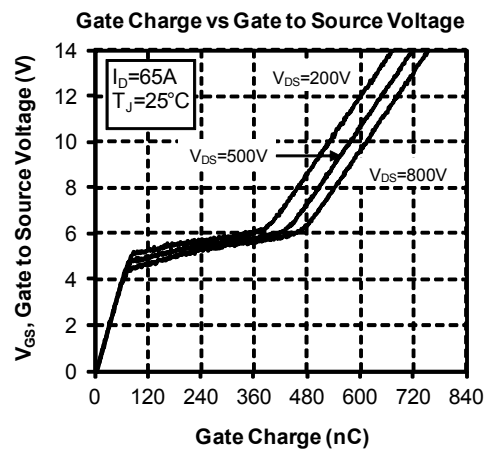
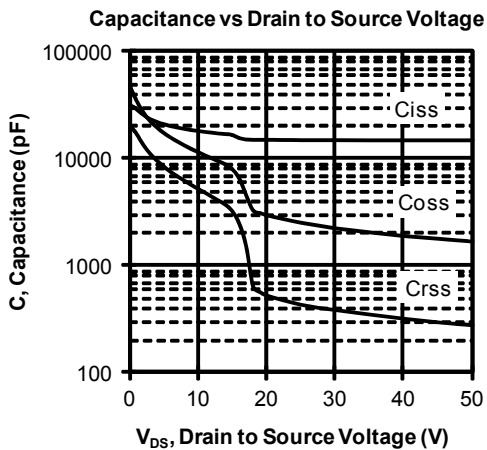
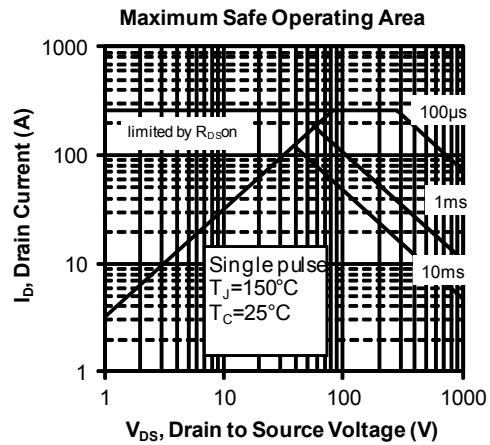
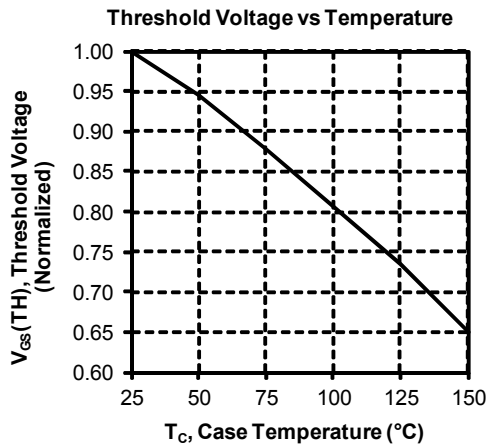
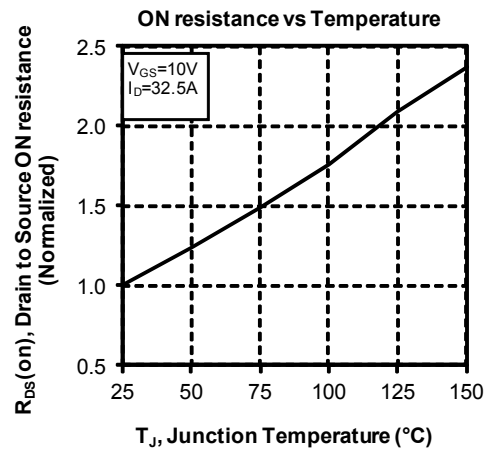
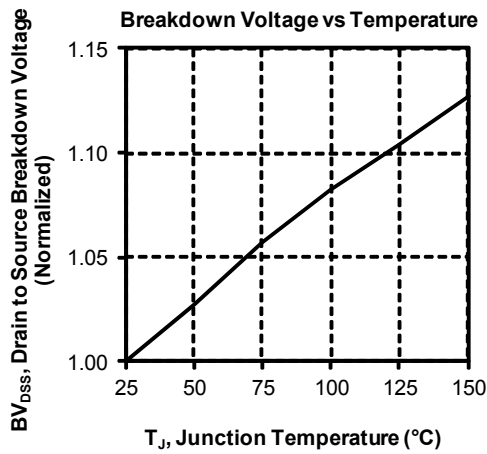
SP6 Package outline (dimensions in mm)

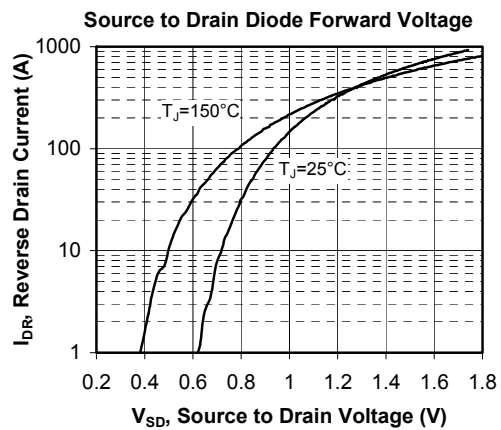
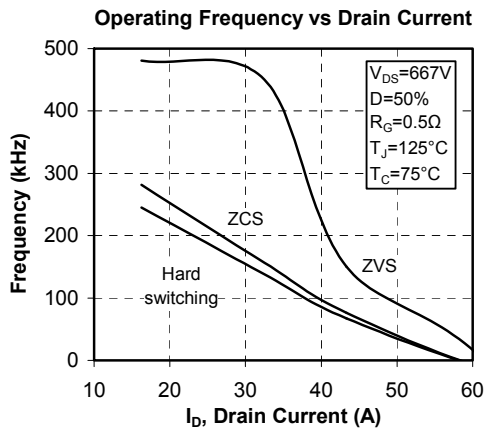
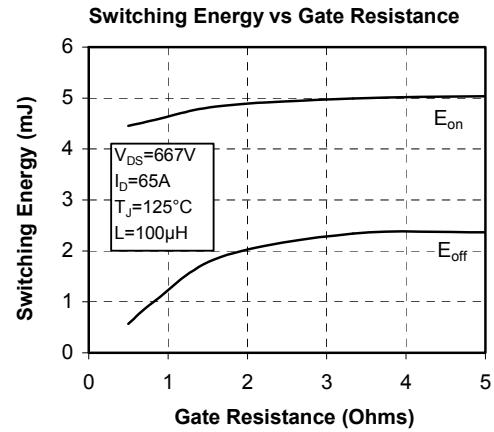
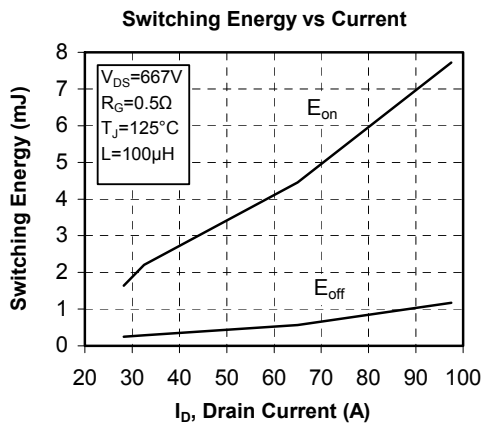
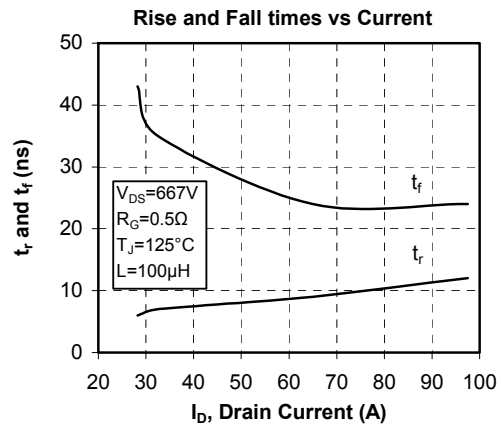
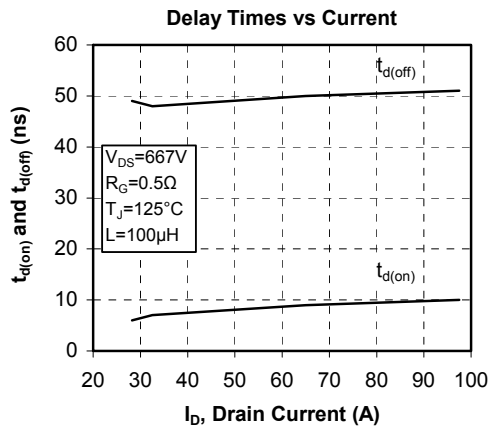


See application note APT0601 - Mounting Instructions for SP6 Power Modules on www.microsemi.com

Typical Performance Curve







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